

BRES4V5M1B2ZP

Rev.C Dec.-2024

描述 / Descriptions

DFN1006-2L 塑封封装单线程双向 ESD 保护二极管。
 DFN1006-2L Plastic Package 1-Line,Bi-directional , ESD Protection Diode.

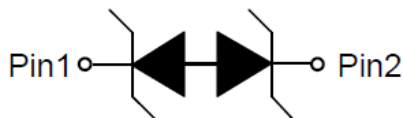
特征 / Features

- ◆ Stand-off voltage: $\pm 4.5V$ Max.
- ◆ Transient protection for each line according to IEC61000-4-2(ESD): $\pm 30kV$ (contact)
 IEC61000-4-4 (EFT): 40A (5/50ns)
 IEC61000-4-5(surge): 37A (8/20 μs)
- ◆ Ultra-low capacitance: $C_J = 65pF$ typ.
- ◆ Low leakage current:
- ◆ Low clamping voltage: $V_{CL} = 7.0V$ typ. @ $I_{PP} = 16A$ (TLP)
- ◆ Solid-state silicon technology
- ◆ HF Product

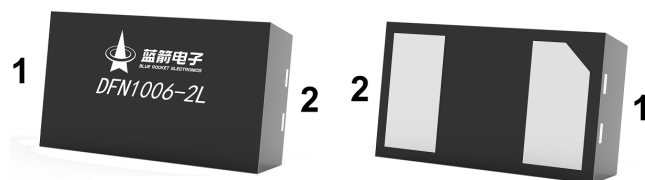
用途 / Applications

- ◆ Cellular handsets
- ◆ Tablets
- ◆ Laptops
- ◆ Other portable devices
- ◆ Network communication devices

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



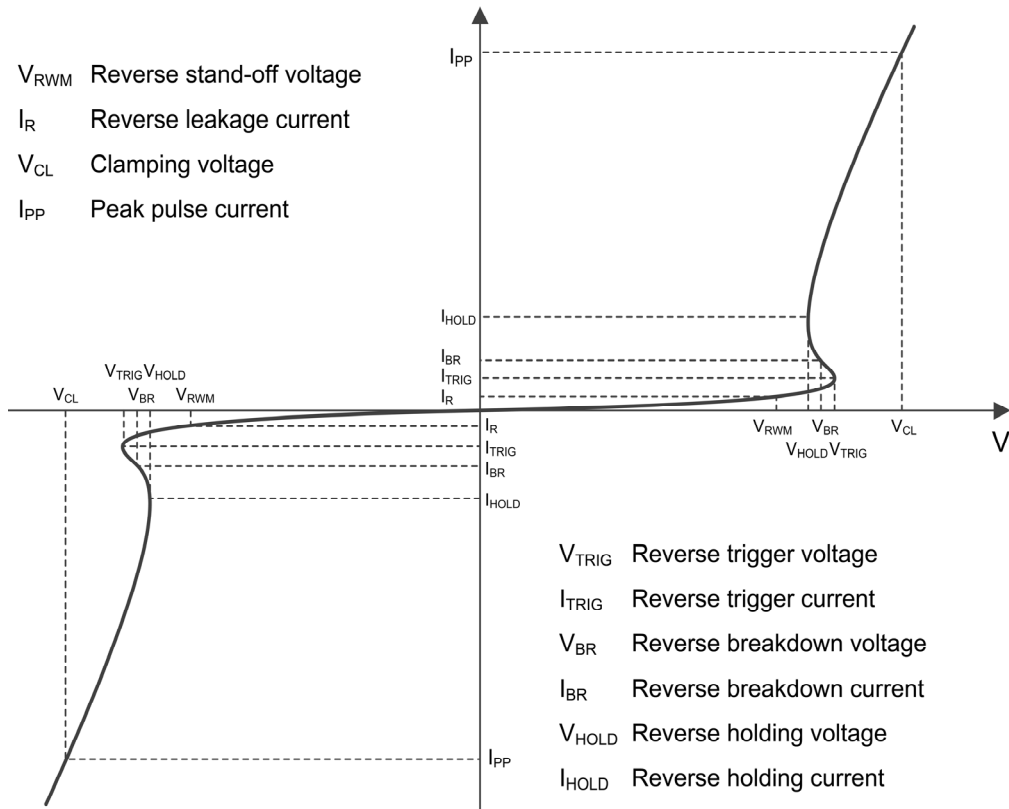
印章代码 / Marking

见印章说明。
 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Peak Pulse Power($t_p = 8/20\mu s$)	P _{PK}	370	W
Peak Pulse Current($t_p = 8/20\mu s$)	I _{PP}	37	A
ESD according to IEC61000-4-2 air discharge	V _{ESD}	±30	KV
ESD according to IEC61000-4-2 contact discharge		±30	
Junction temperature	T _J	125	°C
Operating temperature	T _{OP}	-40~85	°C
Lead temperature	T _L	260	°C
Storage Temperature	T _{STG}	-55~+150	°C

电性能参数 / Electrical Characteristics(Ta=25°C , unless otherwise noted)



Definitions of electrical characteristics

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Reverse maximum working voltage	V _{RWM}				±4.5	V
Reverse leakage current	I _R	V _{RWM} = ±4.5V			0.1	μA
Reverse breakdown voltage	V _{BR}	I _T =1mA	4.6			V
Clamping voltage ¹⁾	V _{CL}	I _{PP} =16A t _p =100ns		7		V
Dynamic resistance ¹⁾	R _{DYN}			0.09		Ω
Clamping voltage ²⁾	V _{CL}	V _{ESD} = 8kV		7		V
Clamping voltage ³⁾	V _{CL}	I _{PP} = 1A t _p = 8/20μs		4.9	6	V
		I _{PP} = 20A t _p = 8/20μs		6.5	8	V
		I _{PP} = 37A t _p = 8/20μs		8.5	10	V
Junction Capacitance	C _J	V _R = 0V f = 1MHz		65	75	pF

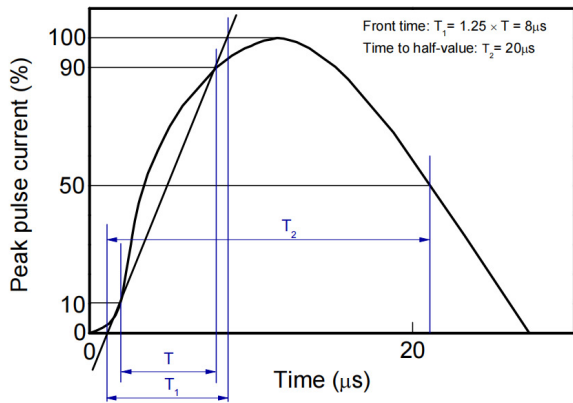
Notes:

1) TLP parameter: Z₀ = 50Ω, t_p = 100ns, t_r = 2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

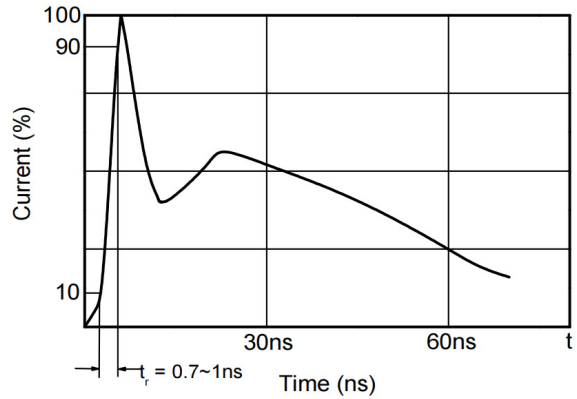
2) Contact discharge mode, according to IEC61000-4-2.

3) Non-repetitive current pulse, according to IEC61000-4-5.

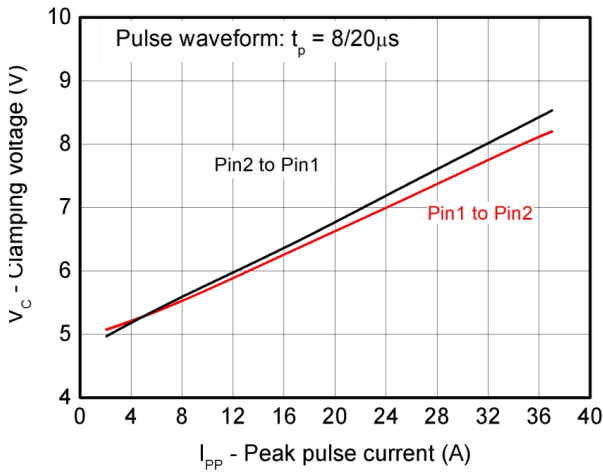
电参数曲线图 / Electrical Characteristic Curve(Ta=25°C , unless otherwise noted)



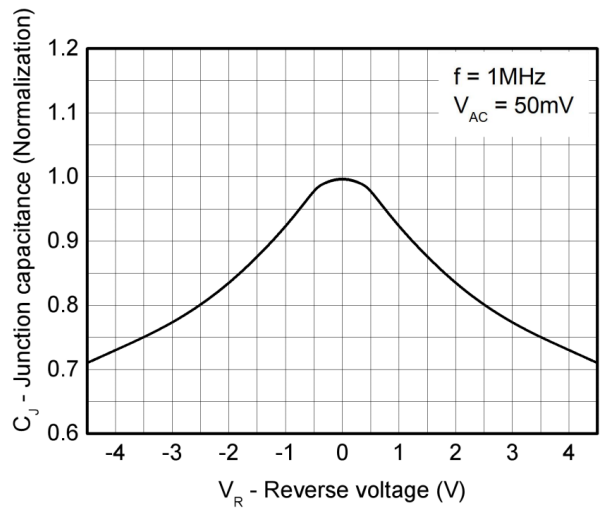
8/20μs waveform per IEC61000-4-5



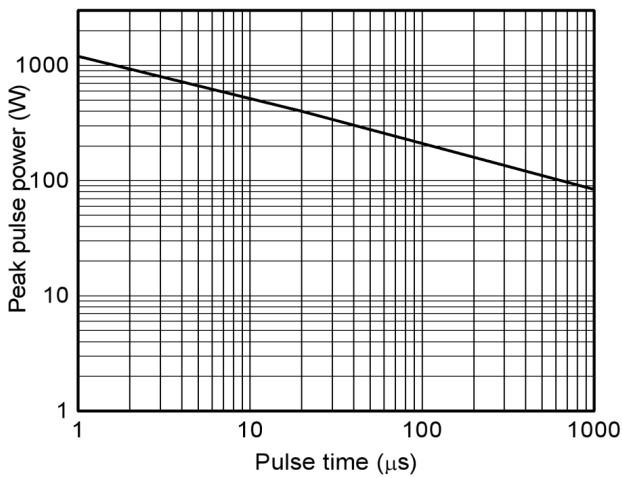
Contact discharge current waveform per IEC61000-4-2



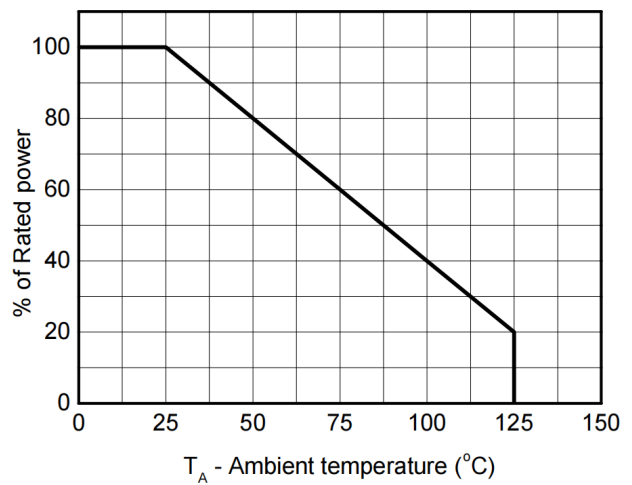
Clamping voltage vs. Peak pulse current



Capacitance vs. Reverse voltage

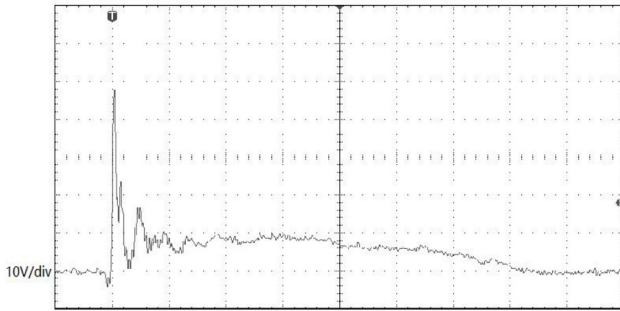


Non-repetitive peak pulse power vs. Pulse time

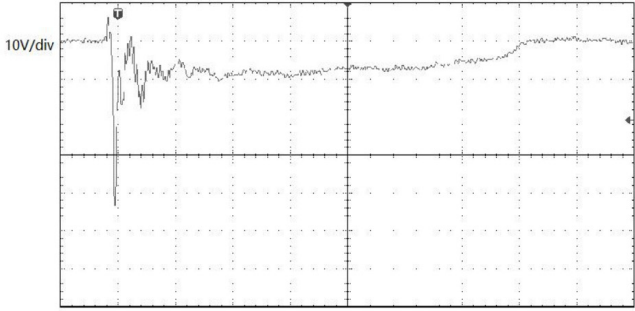


Power derating vs. Ambient temperature

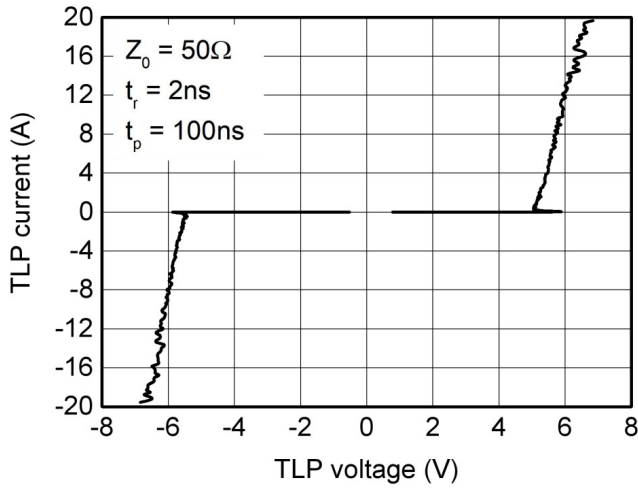
电参数曲线图 / Electrical Characteristic Curve (Ta=25°C , unless otherwise noted)



ESD clamping
(+8kV contact discharge per IEC61000-4-2)



ESD clamping
(-8kV contact discharge per IEC61000-4-2)



TLP Measurement

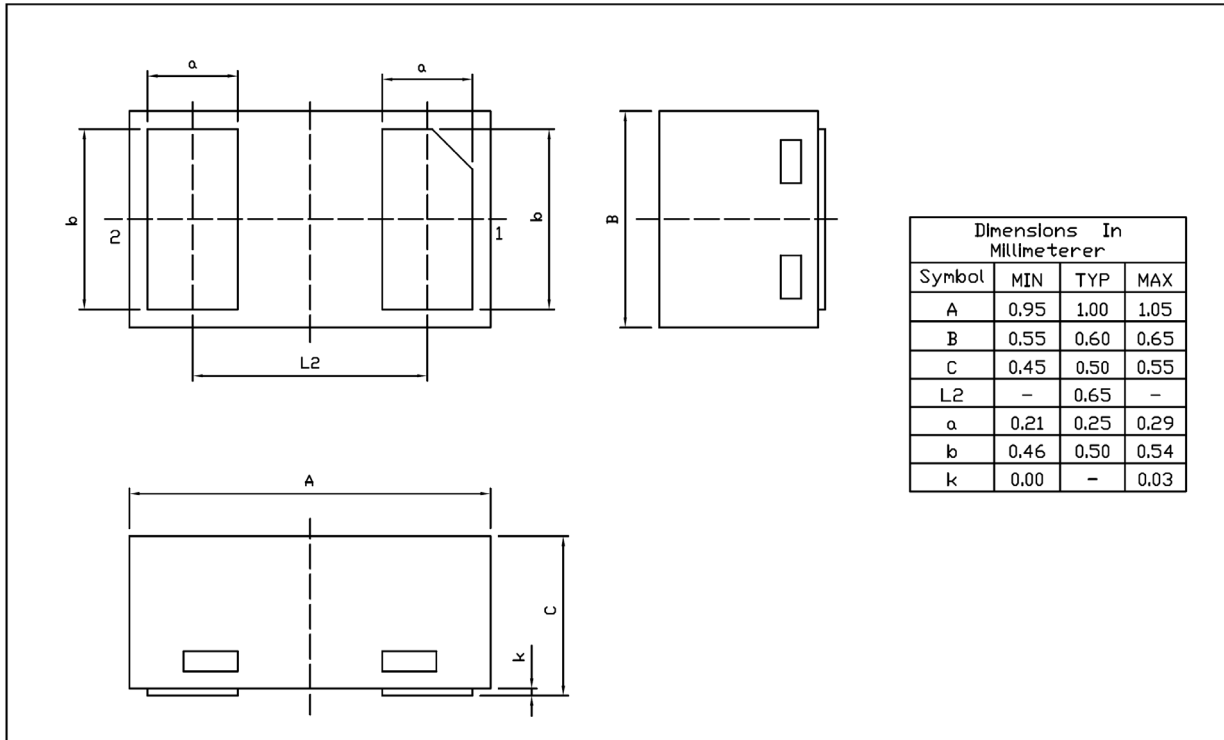
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外形尺寸图 / Package Dimensions

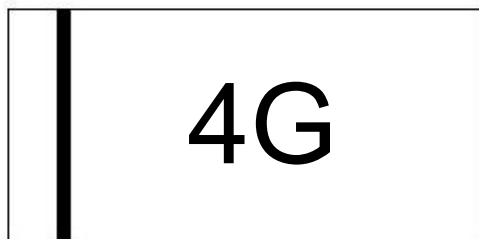
DFN1006-2L

Unit:mm



Rev.01 202108

印章说明 / Marking Instructions



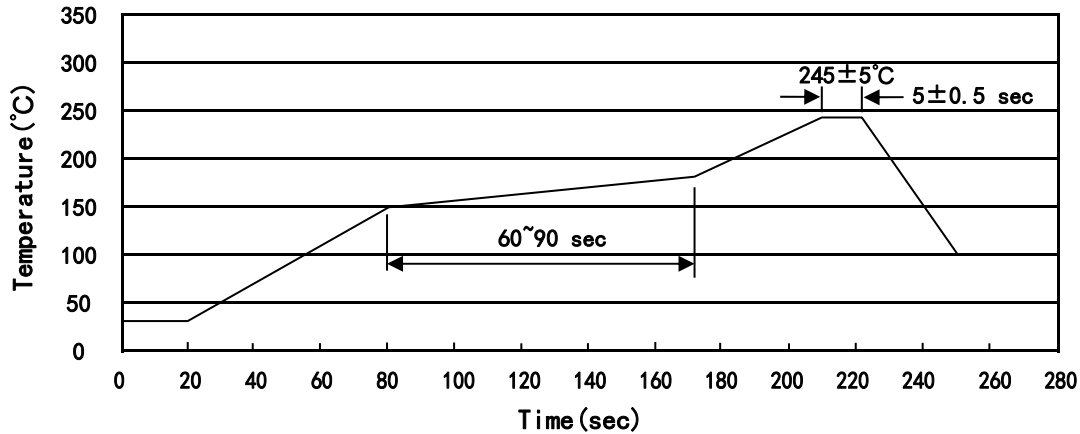
说明：

4G： 为型号代码

Note：

4G： Product Type Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN1006-2L	10,000	10	100,000	6	600,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices